

WHAT IS CLAIMED IS:

Sub  
A17

1. A semiconductor device comprising:  
a filmy resinous substrate;  
a resinous layer provided on said filmy resinous substrate; and  
a semiconductor layer comprising silicon provided over said  
resinous layer.

Sub  
EP

2. The device of claim 1 wherein said semiconductor layer  
constitutes an inverted-staggered thin-film transistor.

3. The device of claim 1 wherein said substrate comprises a  
material selected from the group consisting of polyethylene terephthalate,  
polyethylene naphthalate, polyethylene sulfite and polyimide.

Sub  
B1

4. The device of claim 1 wherein said resinous layer comprises  
a material selected from the group consisting of methyl ester of acrylic  
acid, ethyl ester of acrylic acid, butyl ester of acrylic acid, 2-ethylhexyl  
ester of acrylic acid.

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A27

5. A semiconductor device comprising:  
a filmy resinous substrate;  
a resinous layer provided on said filmy resinous substrate; and  
a thin film transistor comprising a semiconductor layer  
comprising silicon on said resinous layer;  
an interlayer dielectric layer comprising a resinous material  
provided over said semiconductor layer; and

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an indium tin oxide layer provided on said interlayer dielectric layer.

Sub E4

6. The device of claim 5 wherein said substrate comprises a material selected from the group consisting of polyethylene terephthalate, polyethylene naphthalate, polyethylene sulfite and polyimide.

Sub B3

7. The device of claim 5 wherein said resinous layer comprises a material selected from the group consisting of methyl ester of acrylic acid, ethyl ester of acrylic acid, butyl ester of acrylic acid, 2-ethylhexyl ester of acrylic acid.

Sub C3

8. The device of claim 5 wherein said interlayer dielectric layer comprises polyimide.

9. A semiconductor device comprising:  
a filmy resinous substrate;  
a resinous layer provided on said filmy resinous substrate; and  
a semiconductor layer comprising silicon provided over said resinous layer,

wherein said substrate comprises a material selected from the group consisting of polyethylene terephthalate, polyethylene naphthalate, polyethylene sulfite and polyimide.

10. The device of claim 9 wherein said resinous layer comprises a material selected from the group consisting of methyl ester of acrylic acid, ethyl ester of acrylic acid, butyl ester of acrylic acid, 2-ethylhexyl ester of acrylic acid.

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add B6 A37

add E157

add P2